3rd Generation thinQ!™ SiC Schottky Diode

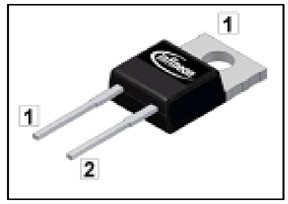
Features

- Revolutionary semiconductor material - Silicon Carbide
- Switching behavior benchmark
- No reverse recovery / No forward recovery
- Temperature independent switching behavior
- High surge current capability
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC[1)] for target applications
- Optimized for high temperature operation
- Lowest Figure of Merit Q_C/I_F

Product Summary

V_{DC}	1200	V
Q_C	7.2	nC
I_F; T_C< 130 °C	2	A

PG-TO220-2



thinQ!™ 3G Diode designed for fast switching applications like:

- SMPS e.g.; CCM PFC
- Motor Drives; Solar Applications; UPS

Type	Package	Marking	Pin 1	Pin 2
IDH02SG120	PG-TO220-2	D02G120	C	A

Maximum ratings

Parameter	Symbol	Conditions	Value	Unit
Continuous forward current	I_F	T_C<130 °C	2	A
Surge non-repetitive forward current, sine halfwave	$I_{F,SM}$	T_C=25 °C, t_p=10 ms	15	
		T_C=150 °C, t_p=10 ms	13	
Non-repetitive peak forward current	$I_{F,max}$	T_C=25 °C, t_p=10 µs	90	
i^2t value	$\int i^2dt$	T_C=25 °C, t_p=10 ms	1.4	A^2s
		T_C=150 °C, t_p=10 ms	1.1	
Repetitive peak reverse voltage	V_{RRM}	T_j=25 °C	1200	V
Diode dv/dt ruggedness	dv/dt	V_R= 0….960 V	50	V/ns
Power dissipation	P_{tot}	T_C=25 °C	75	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 175	°C
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	1.6mm (0.063 in.) from case for 10s	260	
Mounting torque		M3 and M3.5 screws	60	Ncm

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics						
Thermal resistance, junction - case	R_{thJC}		-	-	2	K/W
Thermal resistance, junction - ambient	R_{thJA}	Thermal resistance, junction- ambient, leaded	-	-	62	

Electrical characteristics, at T_j=25 °C, unless otherwise specified

Parameter	Symbol	Conditions	min.	typ.	max.	Unit
Static characteristics						
DC blocking voltage	V_{DC}	I_R=0.05 mA, T_j=25 °C	1200	-	-	V
Diode forward voltage	V_F	I_F=2 A, T_j=25 °C	-	1.65	1.8	
		I_F=2 A, T_j=150 °C	-	2.55	-	
Reverse current	I_R	V_R=1200 V, T_j=25 °C	-	2	48	µA
		V_R=1200 V, T_j=150 °C	-	8	400	
AC characteristics						
Total capacitive charge	Q_c	V_R=400 V, $I_F \leq I_{F,max}$, di_F/dt=200 A/µs, T_j=150 °C	-	7.2	-	nC
Switching time[2]	t_c		-	-	<10	ns
Total capacitance	C	V_R=1 V, f=1 MHz	-	125	-	pF
		V_R=300 V, f=1 MHz	-	12	-	
		V_R=600 V, f=1 MHz	-	10	-	

[1] J-STD20 and JESD22

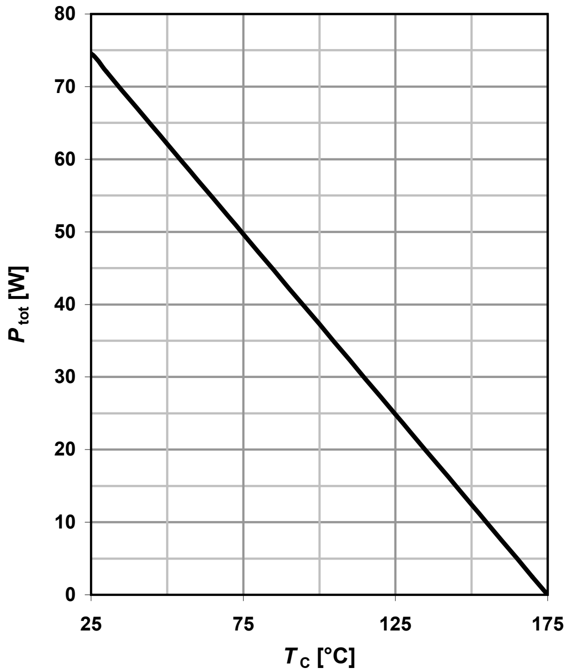
[2] t_c is the time constant for the capacitive displacement current waveform (independent from T_j, I_{LOAD} and di/dt), different from t_{rr} which is dependent on T_j, I_{LOAD} and di/dt. No reverse recovery time constant t_{rr} due to absence of minority carrier inje

[3] Under worst case Z_{th} conditions.

[4] Only capacitive charge occuring, guaranteed by design

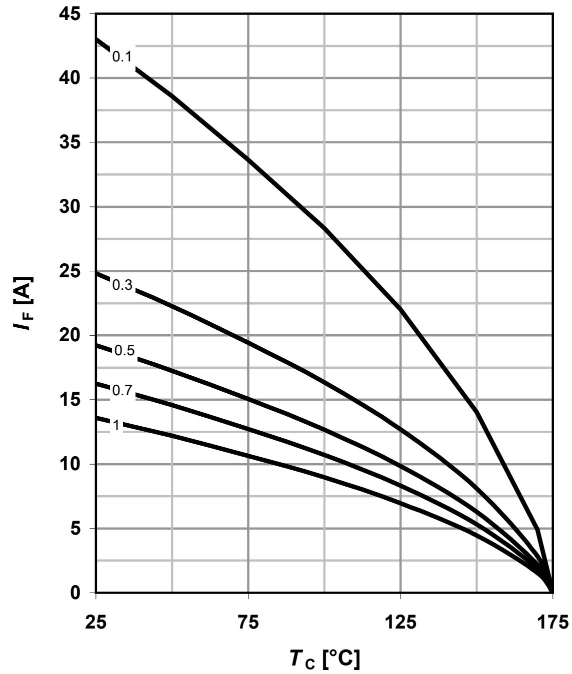
1 Power dissipation

P_{tot}=f(T_C)



2 Diode forward current

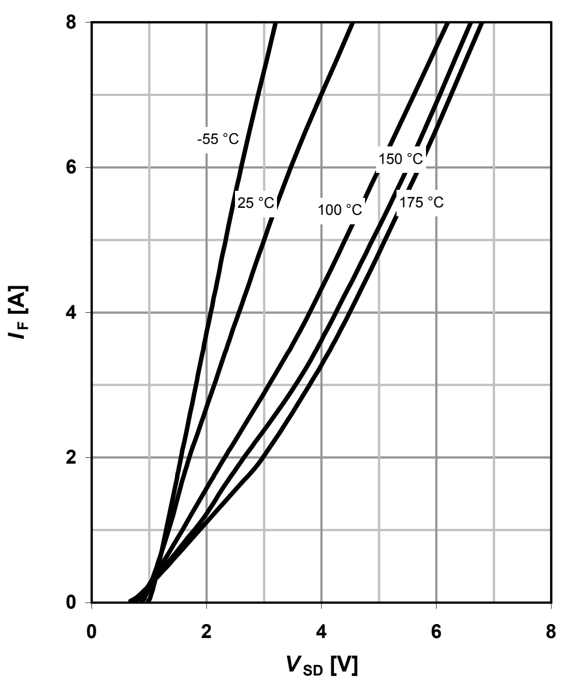
I_F=f(T_C)[3]; T_j≤175 °C; parameter: $D = t_p/T$



3 Typ. forward characteristic

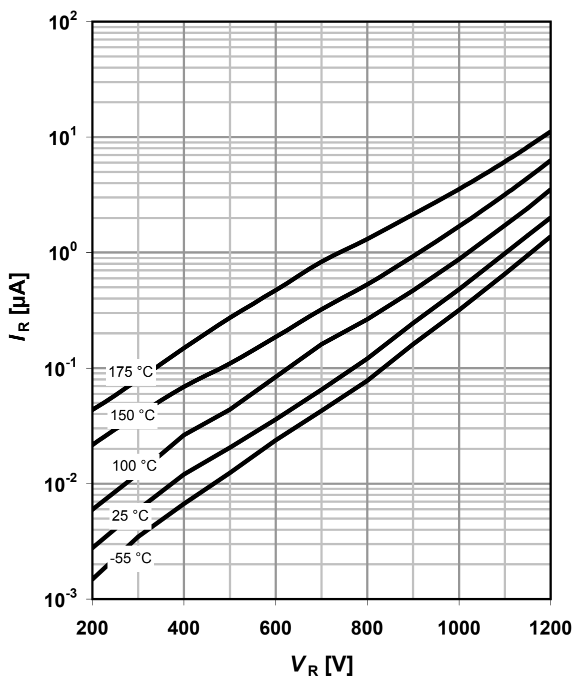
I_F=f(V_F); t_p=400 µs

parameter: T_j



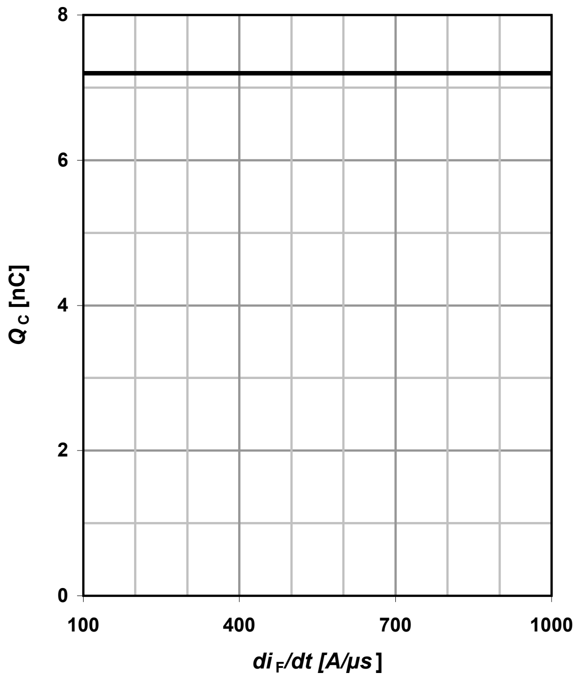
4 Typ. Reverse current vs. reverse voltage

E_C=f(V_R)



5 Typ. capacitance charge vs. current slope

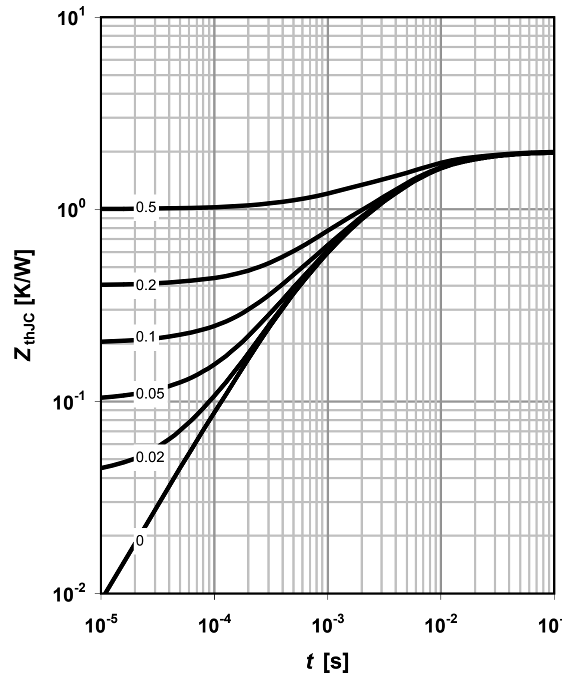
Q_C=f(di_F/dt)[4)]; T_j=150 °C; $I_F \leq I_{F,max}$



6 Transient thermal impedance

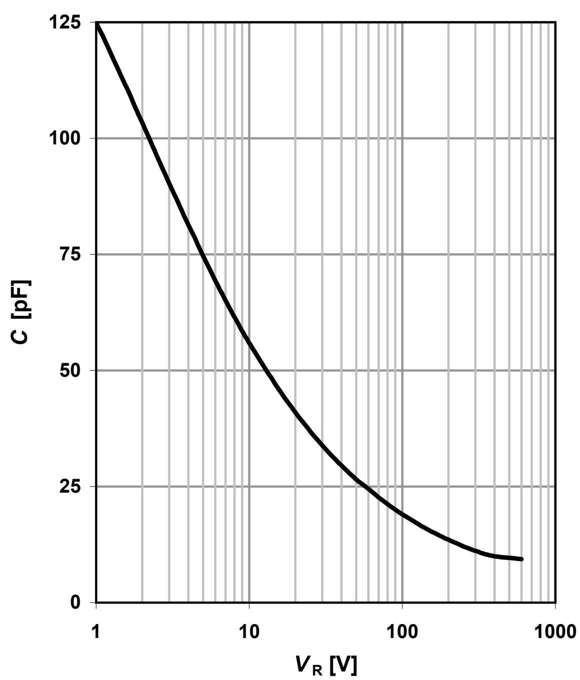
Z_{thJC}=f(t_p)

parameter: $D=t_p/T$



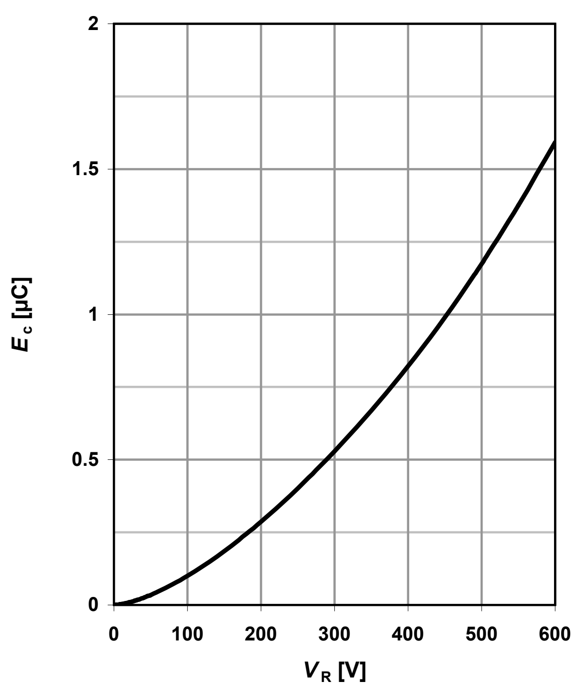
7 Typ. capacitance vs. reverse voltage

C=f(V_R); T_C=25 °C, f=1 MHz

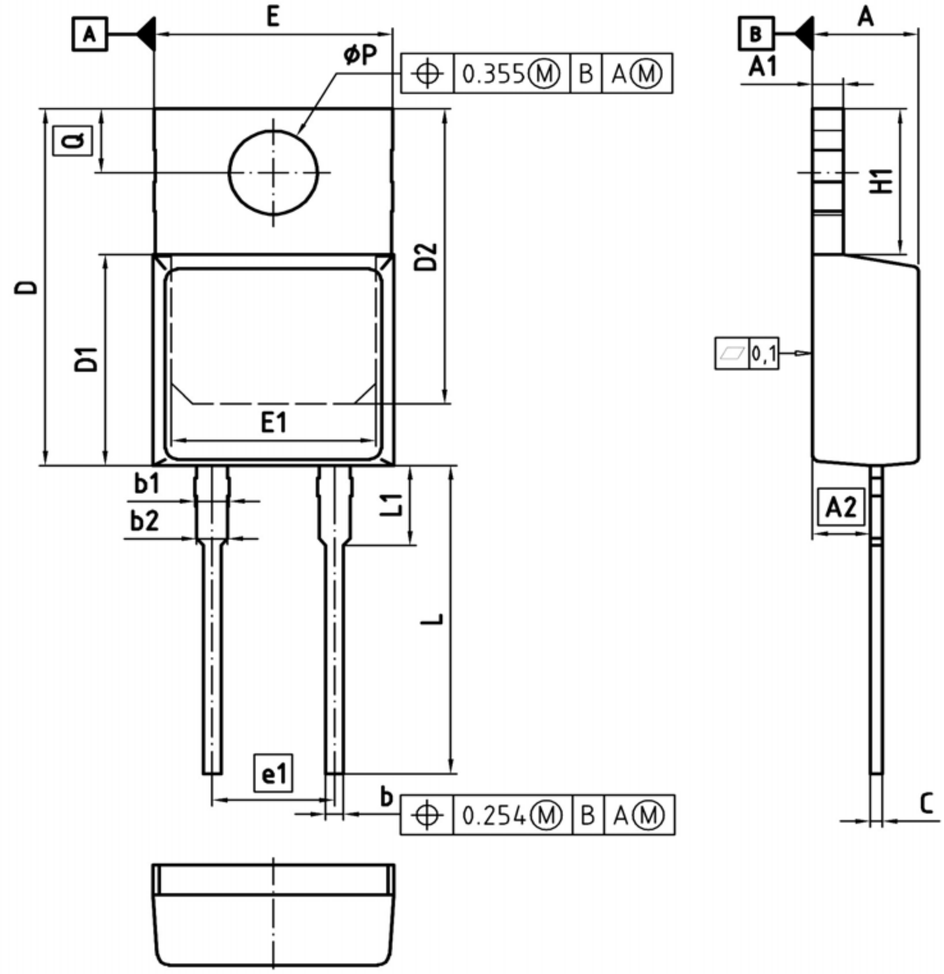


8 Typ. C stored energy

E_C=f(V_R)



PG-TO220-2: Outline



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.50	0.169	0.177
A1	1.17	1.37	0.046	0.054
A2	2.30	2.50	0.091	0.098
b	0.65	0.85	0.026	0.033
b1	1.19	1.69	0.047	0.066
b2	1.19	1.39	0.047	0.055
c	0.40	0.60	0.016	0.024
D	15.35	15.95	0.604	0.628
D1	9.05	9.45	0.356	0.372
D2	12.30	13.05	0.484	0.514
E	9.80	10.20	0.386	0.402
E1	7.25	8.60	0.285	0.339
e1	5.08		0.200	
N	2		2	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	3.30	3.70	0.130	0.146
øP	3.55	3.70	0.140	0.146
Q	2.60	3.00	0.102	0.118

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SCALE 0 2.5 5mm

EUROPEAN PROJECTION

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REVISION
01

Dimensions in mm/inches

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